

IN THE CLAIMS:

Please amend claims 1 and 19 and add new claim 20 as follows:

1. (Currently Amended) A polycrystalline structure film comprising:
metallic islands formed on a surface of a substrate and physically spaced from each other so as to expose a metallic compound ~~among~~ between the metallic islands; and
a ~~metallic seed~~ crystal layer containing crystal grains, each of the crystal grains having grown from a corresponding one of the metallic islands so as to stand from a surface of the metallic compound; and
a magnetic crystal layer containing magnetic crystal grains, each of the magnetic crystal grains having grown from a corresponding one of the crystal grains of the seed crystal layer.

2. (Previously Presented) The polycrystalline structure film according to claim 1, wherein said metallic islands include a metallic compound.

3. (Previously Presented) The polycrystalline structure film according to claim 2, wherein said metallic compound of the metallic islands includes at least one of a metallic nitride and a metallic oxide.

4. (Previously Presented) The polycrystalline structure film according to claim 3, wherein said metallic compound of the metallic islands is any of Si_3N_4 , SiO_2 and Al_2O_3 .

5. (Previously Presented) The polycrystalline structure film according to claim 2, wherein said metallic islands include platinum atoms.

6. (Previously Presented) The polycrystalline structure film according to claim 2, wherein said metallic islands contain said compound in a range between 5at% and 20at%.

7-18. (Cancelled)

19. (Currently Amended) The polycrystalline structure film according to claim 1, wherein each of said crystal grains contact each other contacts with another crystal grain at a grain boundaries boundary, non-magnetic material diffusing along the grain boundary.

20. (New) The polycrystalline structure film according to claim 19, wherein a wall of the non-magnetic material is formed at the grain boundary.